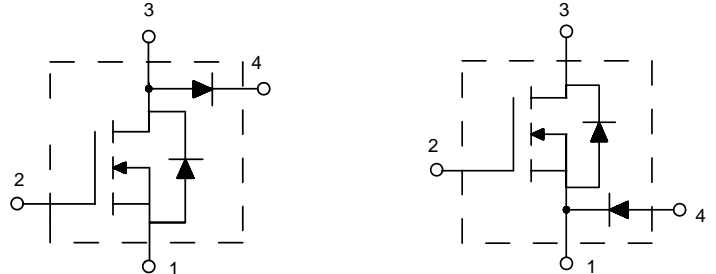


HiPerFET™

Power MOSFETs

	V_{DSS}	I_D (cont)	$R_{DS(on)}$	t_{rr}
IXFN44N50U2 IXFN44N50U3	500 V	44 A	0.12 Ω	35 ns
IXFN48N50U2 IXFN48N50U3	500 V	48 A	0.10 Ω	35 ns

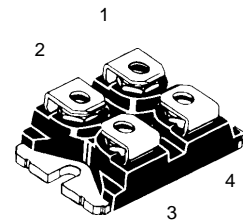
Buck & Boost Configurations for PFC & Motor Control Circuits



Preliminary data

Symbol	Test Conditions	Maximum Ratings			
HiPerFET MOSFET	V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V	
	V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	500	V	
	V_{GS}	Continuous	± 20	V	
	V_{GSM}	Transient	± 30	V	
	I_{D25}	$T_C = 25^\circ\text{C}$	44N50 48N50	44 48	A
	I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by max. T_{JM}	44N50 48N50	176 192	A
	I_{AR}	$T_C = 25^\circ\text{C}$		24	A
	E_{AR}	Repetitive		30	mJ
	dv/dt	$I_S \leq I_{DM}$, $-di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$		5	V/ns
	P_D	$T_C = 25^\circ\text{C}$		520	W
DIODE	V_{RRM}		600	V	
	I_{FAVM}	$T_C = 70^\circ\text{C}$; rectangular, $d = 0.5$	60	A	
	I_{FRM}	$tp < 10\ \mu\text{s}$; pulse width limited by T_J	800	A	
	P_D	$T_C = 25^\circ\text{C}$	180	W	
CASE	T_J		-40 ... +150	$^\circ\text{C}$	
	T_{JM}		150	$^\circ\text{C}$	
	T_{stg}		-40 ... +150	$^\circ\text{C}$	
	V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ min}$ $t = 1\text{ s}$	2500 3000	V~ V~
	M_d	Mounting torque Terminal connection torque (M4)		1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight			30	g	

miniBLOC, SOT-227 B



Features

- Popular Buck & Boost circuit topologies
- International standard package miniBLOC SOT-227B
- Aluminium nitride isolation - high power dissipation
- Isolation voltage 3000 V~
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF) - reduced RFI
- Ultra-fast FRED diode with soft reverse recovery

Applications

- Power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

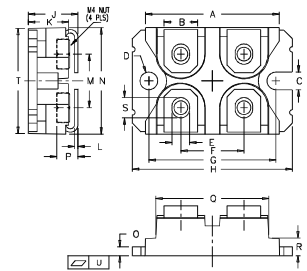
Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled FRED

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 8\text{ mA}$	2		V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}, V_{DS} = 0$			± 200 nA
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$ $V_{GS} = 0\text{ V}$		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	400 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$		44N50 48N50	0.12 Ω 0.10 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}, I_D = 0.5 I_{D25}$, pulse test	22	42	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8400	pF
C_{oss}			900	pF
C_{rss}			280	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External)		30	ns
t_r			60	ns
$t_{d(off)}$			100	ns
t_f			30	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		270	nC
Q_{gs}			60	nC
Q_{gd}			135	nC
R_{thJC}		0.24		K/W
R_{thCK}		0.05		K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_R	$T_J = 25^\circ\text{C}; V_R = V_{RRM}$ $V_R = 0.8 V_{RRM}$ $T_J = 125^\circ\text{C}; V_R = 0.8 V_{RRM}$			200 μA 100 μA 14 mA
V_F	$I_F = 70\text{ A}, V_{GS} = 0\text{ V}, T_J = 150^\circ\text{C}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$ $T_J = 25^\circ\text{C}$			1.5 V 1.8 V
t_{rr}	$I_1 = 1\text{ A}, di/dt = -200\text{ A}/\mu\text{s}, V_R = 30\text{ V}, T_J = 25^\circ\text{C}$		35	50 ns
I_{RM}	$I_F = 60\text{ A}, di/dt = -480\text{ A}/\mu\text{s}, V_R = 350\text{ V}, T_J = 100^\circ\text{C}$		19	21 A
R_{thJC}				0.7 K/W
R_{thJK}			0.05	K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Fig.1 Output Characteristics

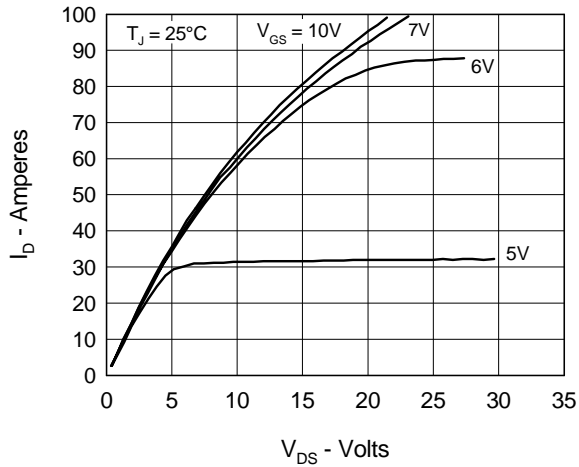


Fig.2 Input Admittance

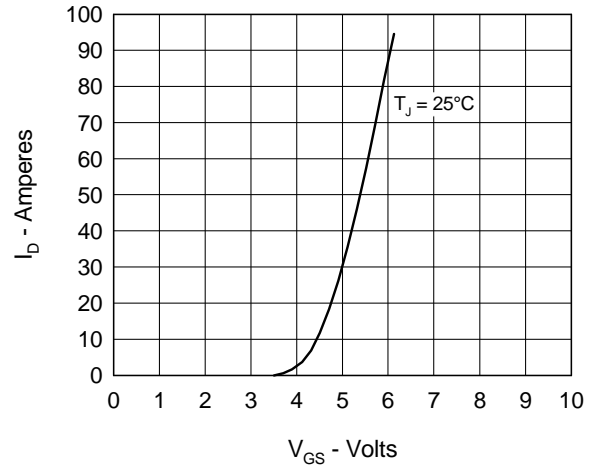


Fig.3 $R_{DS(on)}$ vs. Drain Current

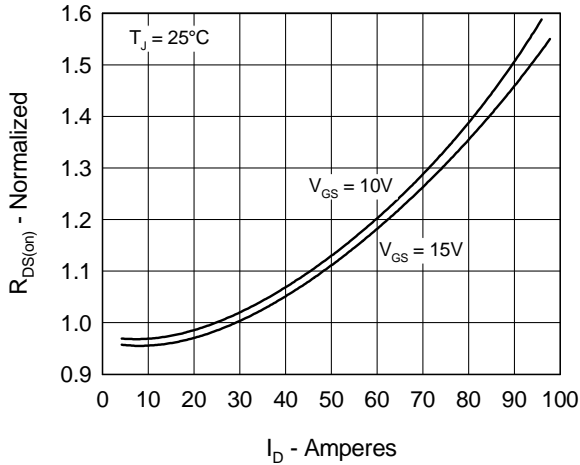


Fig.4 Temperature Dependence of Drain to Source Resistance

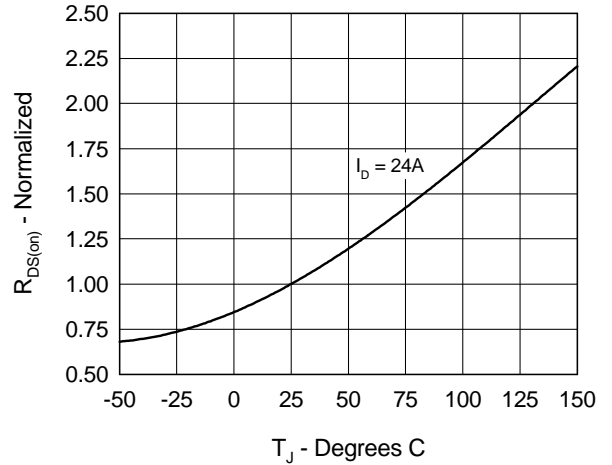


Fig.5 Drain Current vs. Case Temperature

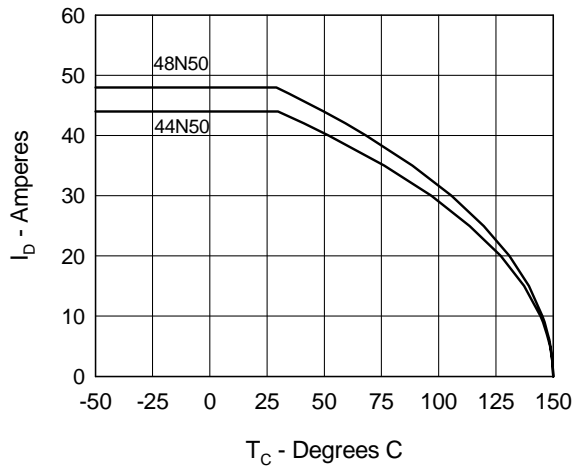


Fig.6 Temperature Dependence of Breakdown and Threshold Voltage

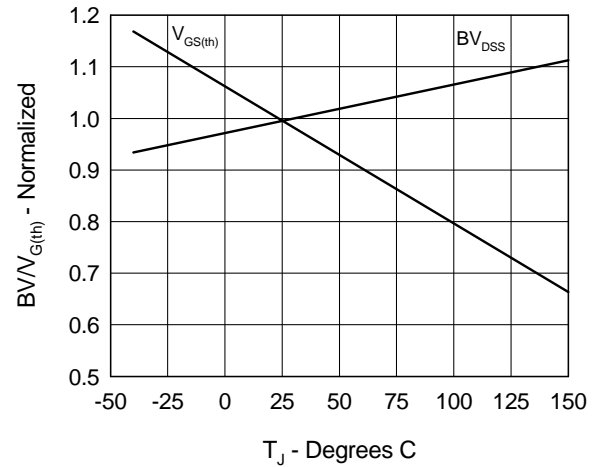


Fig.7 Gate Charge Characteristic Curve

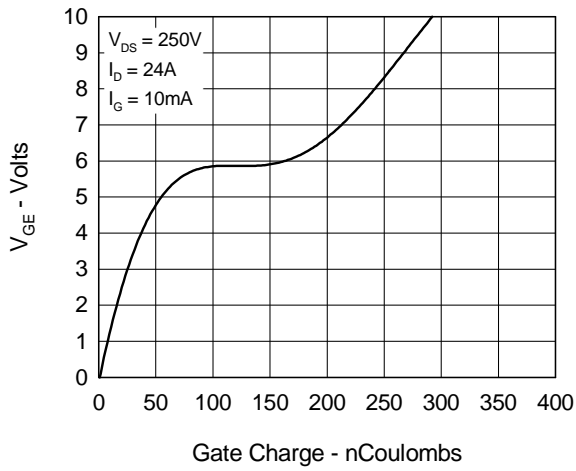


Fig.8 Capacitance Curves

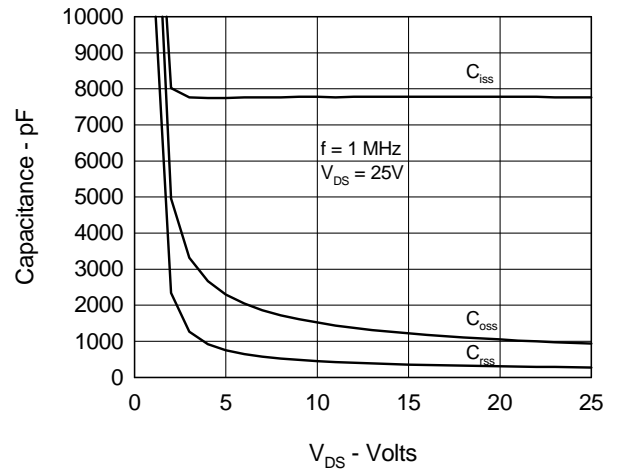


Fig.9 Source Current vs. Source to Drain Voltage

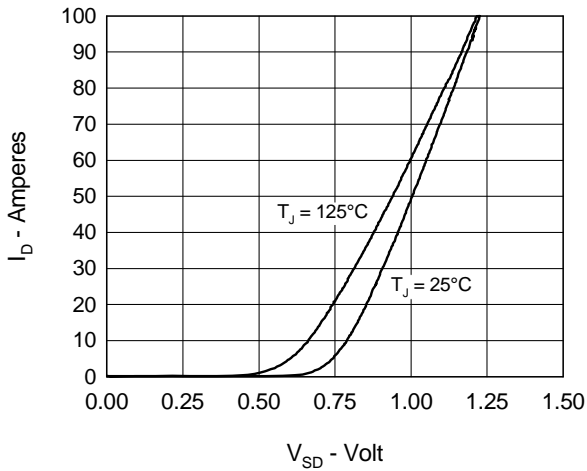
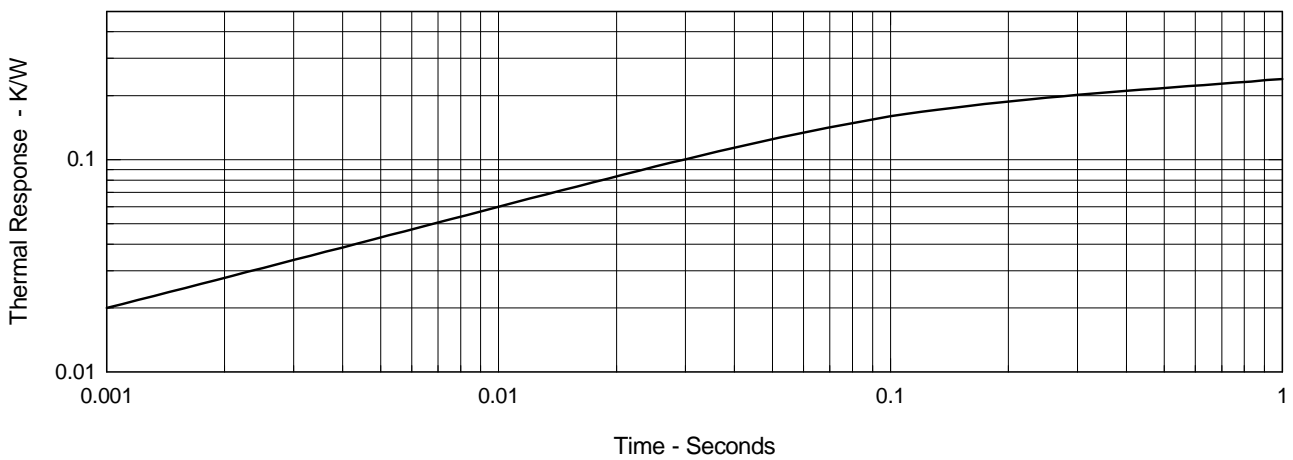


Fig.10 Transient Thermal Impedance



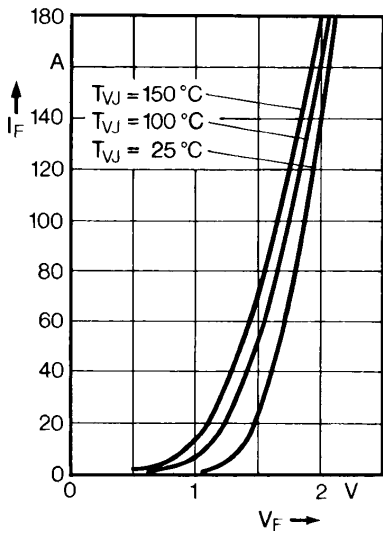


Fig. 11. Forward voltage drop.

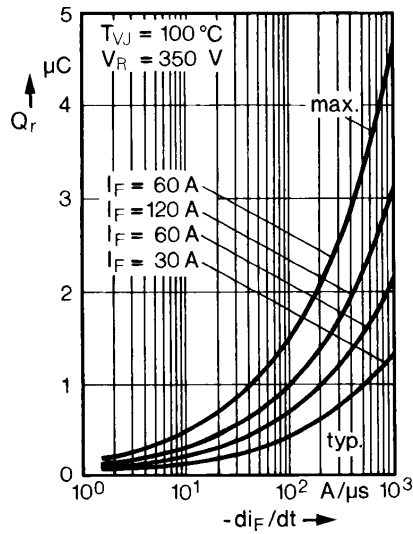


Fig. 12. Recovery charge versus $-di_F/dt$.

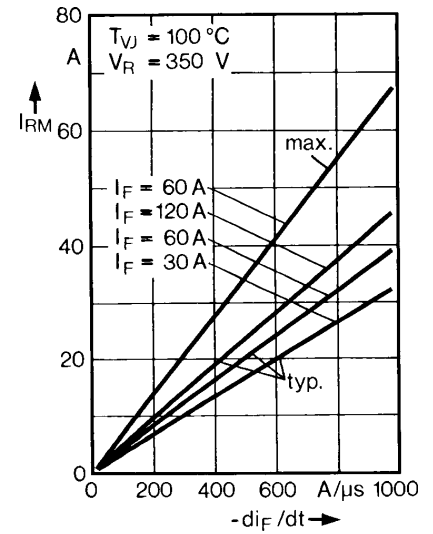


Fig. 13. Peak reverse current vs. $-di_F/dt$.

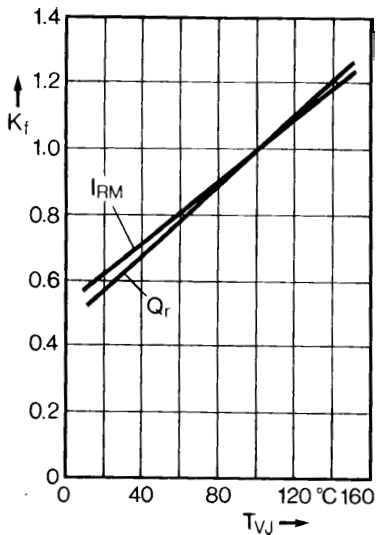


Fig. 14. Dynamic parameters versus junction temperature.

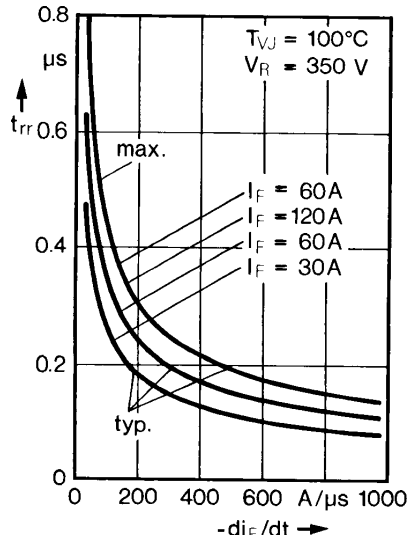


Fig. 15. Recovery time versus $-di_F/dt$.

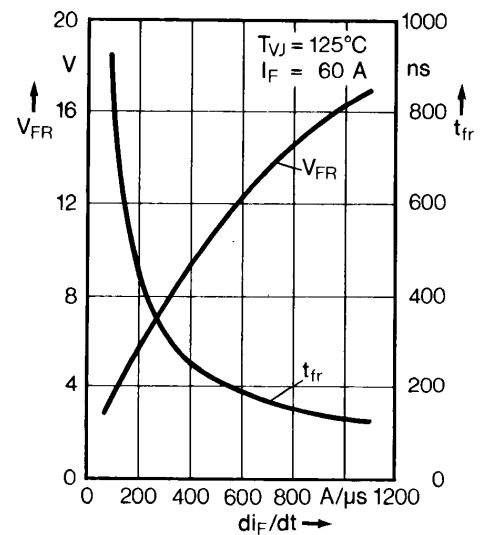


Fig. 16. Peak forward voltage and forward recovery time vs. di_F/dt .

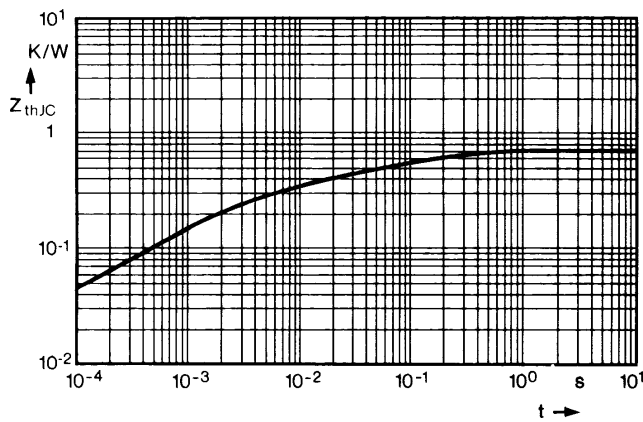


Fig. 17. Transient thermal impedance junction to case.